MB64 64K Static RAM Board

User's Manual

MB64™ 64K STATIC RAM S-100 Bus

USER'S MANUAL

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1.0 INTRODUCTION

The SSM MB64 represents a significant advance in low-cost, high-density, static memory boards. It incorporates such features as bank select, extended addressing, diagnostic LEDs, and a provision for battery backup.

The MB64 is configurable as two 32K byte bank-switched memory blocks, or 64K bytes of memory with standard or extended addressing. The MB64 can be disabled in 2K increments by the use of a Magic Mapping™ circuit to provide memory space for other memory-mapped devices within the computer system. This board is equipped to sense the phantom disable line to prevent hardware conflicts with auxiliary system boot ROMs on another 696 compatible board.

Features:

- Two 32K byte memory blocks
- Low power CMOS RAM chips (HM6116P)
- High speed access, approximately 150 nsec.
- e Bank switching circuity to support MP/M, CROMIX, OASIS, etc.
- Extended addressing to support IEEE 696 products
- e LED indicators for RAM select and bank select
- Low power consumption of less than 300 ma typical
- © Up to 8K of the top 32K can be replaced with EPROM (2716 type) on-board
- Card ejectors
- Goldplated PCB edge connector

The board has been designed to conform to the proposed IEEE 696 standard.

Magic Mapping is a trademark of SSM Microcomputer Products, Inc. CROMIX is a trademark of Cromemco, 280 Bernardo Avenue, Mountain View, CA. OASIS is a trademark of Phase One Systems, 7700 Edgewater Drive, Oakland, CA. MP/M is a tademark of Digital Research, P.O. Box 579, Pacific Grove, CA.



2.0 SETTING UP YOUR MB64

This section provides the information necessary to configure the MB64 to your particular application. Section 2.9 provides several example setups to assist you in performing this task. Be sure to also read Section 2.10, SWO OPTION, for proper read/write operation of the MB64 with your CPU.

NOTE: All of the following options (except BANK BIT) can be selected either by using supplied mini-jumpers or wire-wrapping.

2.1 MEMORY ADDRESSING

The MB64 is divided into two memory blocks of 32K bytes each. Block-A is physically located on the left half of the board; Block-B is physically located on the right half. Refer to the Memory Map in the APPENDIX for the address location of each memory chip.

Each 32K block can be addressed to either the lower or upper portion of the 64K memory space. Both 32K blocks can be addressed to the same address space if the MB64's Bank Select option is used and the bank bit for each block is different (refer to Section 2.3).

ADDRESS	BLOCK-B	BLOCK-A
Upper 32K	E17 to E18	E20 to E21
Lower 32K	E18 to E19	E21 to E22
Block Disabled	E18 open	E21 open

2.2 EXTENDED ADDRESSING

The MB64 is designed to support extended addressing (A16 thru A23) as defined in the proposed IEEE 696 standard. This will allow the MB64 to be placed on any 64K boundary within a maximum memory space of 16 megabytes.

The Extended Addressing option is enabled by connecting E26 to E27 for Elock-A, and E29 to E30 for Block-B.

To select the extended address range which will enable the MB64, jumpers will be either installed or removed on the header El thru El6 listed below.

Installing a jumper will provide a match when that particular address line is at a logic zero (low). Removing a jumper will provide a match when that particular address line is at a logic one (high).

Jumper installed = 0 Jumper removed = 1

ADDRESS	A2 3	A2 2	A2 1	A2 0	A19	A18	A1 7	A 16	ADDRESS
(Hex)	K9 K1	E10 E2	E1 1 E3	E1 2 E4	E13 E5	E1 4 E6	E1 5 E7	E1 6 E8	RANGE
000000	0	0	0	0	0	0	0	0	1st 64K
010000	0	0	0	0	0	0	0	1	2nd 64K
020000	0	0	0	0	0	0	1	0	3rd 64K
030000	0	0	0	0	0	0	1	1	4th 64K
040000	0	0	0	0	0	1	0	0	5th 64K
FE0000 FF0000	1 1	1 1	1 1	1 1	1 1	1 1	1 1	0 1	255th 64K 256th 64K

When Extended Addressing is selected, Bank Select is disabled; therefore, Bank Select and Extended Addressing are not possible together for the same memory block.

2.3 BANK SELECT

To extend the amount of memory available for an 8-bit CPU, Bank Select can be used on the MB64. This memory management technique switches in and out a 64K bank of memory by writing to an I/O port. Multiple 32K blocks, on one or more MB64s, can be addressed to the same address space, but only ONE block will be active at a time. All bank control is done through port 40 Hex (or 41 Hex). When Bank Select is selected, extended addressing is disabled; therefore, bank select and extended addressing are not possible together on the same memory block.

2.3.1 Bank Select Enable

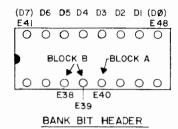
The two 32K blocks of memory on the MB64 can be individually bank selected. E26 thru E28 controls Block-A, while E29 thru E31 controls Block-B.

OPTION	BL OC K-A	в гос к-в
Bank Select	E27 to E28	E30 to E31
Extended Addressing	E26 to E27	E29 to E30
Neither option	E27 open	E30 open

2.3.2 Bank Bit

One of 8 bits sent out to I/O port 40 Hex can be used to turn on (or off) a 64K bank of memory. If the data bit sent is a zero, the bank is disabled. If the data bit sent is a one, the bank is enabled.

All bank bit selection is through a 16 pin IC header. Pins E41 to E48 are data bits D7 thru D0, respectfully. Pin E40 is for banking Block-A, and pin E38 & E39 are for banking Block-B.



Connect pins E38, E39 and E40 to the data bit desired by soldering a wire on the IC header. If only one bank bit is used for Block B, you can jumper E38 to E39. Be careful that pins E41 thru E48 **DO NOT SHORT TOGETHER.** Pins E41 thru E48 are the main S-100 bus' data output lines, and shorting them together may cause damage to other boards in your system.

2.3.3 Power-Up State

In a bank selected memory management system, one of the memory banks must be active on power-up to allow normal CPU operation. Each block on the MB64 can be set up to be enabled or disabled on reset (bus pin 75) of the computer.

POWER-UP STATE	BLOCK-A	BLOCK-B	
Disabled	E35 to E36	E33 to E34	
Enabled	E36 to E37	E32 to E33	

If the Bank Select option is used on the MB64, the user MUST select one of the Power-Up options for each block. [NOTE: Reset must be generated on power-up of the computer during POC per the IEEE 696 standard.]

2.4 EPROM OPTION

The MB64 board is capable of supporting up to four 2716 EPROMs. Four IC sockets (U7, U14, U21, U28) have been provided with a jumper option to connect the Vpp (programming pulse) pin on the EPROM to +5 volts. The four IC sockets are addressed as the top 8K bytes of Block-B.

Address	RAM	ROM	Socket
1st 2K of 8K	E50 to E51	E49 to E50	U28
2nd 2K of 8K	E53 to E54	E52 to E53	U21
3rd 2K of 8K	E56 to E57	E55 to E56	U14
4th 2K of 8K	E59 to E60	E58 to E59	U7

[Remember that there are **NO** wait cycles generated by the MB64 for the EPROMs; therefore, the board cannot be run any faster than the EPROM's speed.]

2716 Manufacturers

		CUR	AVAILABLE	
NAME	PART	STANDBY	READ	SPEED
Intel	2716	25ma (10ma Typ.)	100ma (57ma Typ.)	350ns to 650ns
NEC	UPD 27 16	25ma (10ma Typ.)	100 ma (57 ma Typ.)	450ns
Motorola	MCM2716	25ma	100ma	250ns
AMI	S4716	25ma	100ma	450ns
Fujitsu	MBM2716	25ma	100ma	450ns
Hitachi	HN462716	35ma (21ma Typ.)	100ma (62ma Typ.)	450ns
National	NMC 27 C 16	200ua	30ma (12ma Typ.)	450ns to 650ns

2.5 2K MEMORY DISABLE/MEMORY ORGANIZATION

The MB64 board is equipped with a special Magic Mapping circuit which allows the board to be disabled in 2K byte increments by simply removing the appropriate memory IC. This allows the user to free up memory space for memory-mapped devices such as disk interfaces, video boards, general I/O, ROM boards, etc.

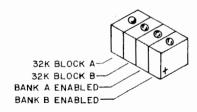
Magic Mapping relies on the **assumption** that the master CPU board has external pull-up resistors on the data input (DI) lines or the computer system has a **terminated bus**. The pull-up resistors on the DI bus will force the bus to "FF" Hex state, even if no S-100 board is present. Therefore, "FF" does not have to be transferred from the memory board to the data input bus. The code "FF" Hex is used internally by the MB64 to disable the ability to read the memory.

To determine which memory chip should be removed for a particular free address space, refer to the memory location map in the APPENDIX.

If the user wants to disable Magic Mapping for some reason, simply remove IC U44 (74LS30).

2.6 BOARD ENABLE INDICATOR

The MB64 has 4 memory state indicators at the top edge of the board. Two indicators show whether a 32K block of memory is selected. Two indicators show whether the bank for a block is enabled.



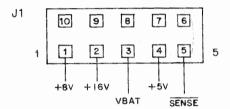
If the MB64 is set up for Bank Select (Section 2.3), both the block LED (label: ENA, ENB) and bank LED (label BNK A, BNK B) must be lit to read or write to the corresponding 32K bytes of memory.

2.7 BATTERY CONNECTOR J1

The MB64 is set up for a future battery backup piggyback board which will interface through connector J1. The connector J1 is used for:

- . Battery power input (VBAT)
- . Remote MB64 enable/disable (Sense)
- . Off-board logic power (+5V)
- . Battery charger power (+16V)
- . General purpose power (+8V)

When no battery backup is connected to the MB64, J1 pin 5 to pin 6 (sense) must be shorted together to enable the MB64. Also, J1 pin 3 to in 4 must be connected to supply power to the memory chips when no battery power is available.



BATTERY CONNECTOR

2.8 SETUP FOR CROMIX

The MB64 can be set up to support the "User Memory" requirements of the CROMIX operating system by Cromemco. Under CROMIX, there can be up to 6 user memory boards of 64K bytes each. CROMIX requires bank-switched memory, with the upper 32K residing in the selected user space and also in the common memory bank (number 7).

The MB64 is split into two 32K banks called "A" and "B". Bank-A will be addressed to low memory range, while Bank-B will be addressed to the upper 32K range. Bank-B has two bank bit inputs (E38 & E39) so that it can be switched into two different banks per CROMIX. First, set up the MB64 for 64K with bank switching, and then select the bank bits for the user memory you are supporting. Typical setup is as follows:

64K Banked Slave Memory

CONNECT	COMMENT
E17 to E18 E21 to E22 J1-3 to J1-4 J1-5 to J1-6 E27 to E28 E30 to E31 E39 to E40 E35 to E36 E33 to E34 E24 to E25 E38 to E41	Enable upper 32K Enable lower 32K Enable memory power Enable MB64 (battery chip select) Enable Bank-A mode Enable Bank-B mode Set both bank bits the same Reset Bank-A to OFF Reset Bank-B to OFF Enable SWO signal Enable upper 32K at Bank 7

User Memory Setup

USER	CONNECT	CROMIX SIZE
1st 2nd 3rd 4th 5th 6th	E40 to E47 E40 to E46 E40 to E45 E40 to E44 E40 to E43 E40 to E42	One user system Two " " Three " " Four " " Five " " Six " "

2.9 STANDARD SETUP

In this section we will try to show some standard configurations for the ${\tt MB64.}$

2.9.1 64K memory, no options

CONNECT	COMMENT
E17 to E18 E21 to E22	Enable upper 32K bytes Enable lower 32K bytes
J1-3 to J1-4 J1-5 to J1-6 E35 to E36	Enable memory power Enable MB64 (battery chip select) Reset Bank-A (turn off LED)
E33 to E34 E50 to E51	Reset Bank-B (turn off LED) Set U28 as RAM
E53 to E54 E56 to E57 E59 to E60	Set U21 as RAM Set U14 as RAM Set U7 as RAM

2.9.2 60K memory with top 4K EPROM

CONNECT	COMMENT
E17 to E18 E21 to E22 J1-3 to J1-4 J1-5 to J1-6 E34 to E36 E33 to E34 E55 to E56 E58 to E59 E50 to E51 E53 to E54	Enable upper 32K bytes Enable lower 32K bytes Enable memory power Enable MB64 (battery chip select) Reset Bank-A (turn off LED) Reset Bank-B (turn off LED) Set U14 as a ROM socket Set U7 as a ROM socket Set U28 as RAM Set U21 as RAM

Remove U7 and U14 RAM chips. Place first 2K of EPROM (2716) into socket U14. U14's socket is addressed at 0F000 Hex. Place second 2K of EPROM into socket U7. U7's socket is addressed at 0F800 Hex. Remember that the CPU's speed cannot be any greater than the access time of the onboard EPROMs unless wait states can be preset on the CPU or other 696 memory support boards.

2.9.3 Bottom 32K banked with top 32K master

CONNECT	COMMENT
E17 to E18	Enable upper 32K bytes
E21 to E22	Enable lower 32K bytes
J1-3 to J1-4	Enable memory power
J1-5 to J1-6	Enable MB64 (batter chip select)
E35 to E36	Reset Bank-A
E33 to E34	Reset Bank-B (turn off LED)
E27 to E28	Enable Bank-A mode
E40 to *	Select bank bit
E50 to E51	Set U28 as RAM
E53 to E54	Set U21 as RAM
E56 to E57	Set Ul4 as RAM
E59 to E60	Set U7 as RAM

^{*} Select bank bit per Section 2.3.2.

This setup makes the top 32K of memory a permanent (non-banked) master, while the lower 32K of memory is bank selected. The lower 32K of memory is switched off during reset or power-up, but can be turned on if E35 to E36 is changed to E36 to E37.

2.9.4 Two 32K banks, lower address

CONNECT	COMMENT
E18 to E19 E21 to E22 J1-3 to J1-4 J1-5 to J1-6 E35 to E36 E33 to E34	Enable lower 32K bytes (Block B) Enable lower 32K bytes (Block A) Enable memory power Enable MB64 (battery chip select) Reset Bank-A Reset Bank-B
E27 to E28 E30 to E31 E40 to * E39 to * E38 to E39 E50 to E51 E53 to E54	Enable Bank-A mode Enable Bank-B mode Select bank bit for A Select bank bit for B Strap up used input Set U28 as RAM Set U21 as RAM
E56 to E57 E59 to E60	Set U14 as RAM Set U7 as RAM

^{*} Select bank bit per Section 2.3.2.

2.9.5 48K banked slave memory

16K of memory (from Block-B) will be removed from the MB64 to make it a 48K only board.

CONNECT	COMMENT
E17 to E18 E21 to E22 J1-3 to J1-4 J1-5 to J1-6 E27 to E28 E30 to E31 E39 to E40 E38 to E39 E38 to * E35 to E36 E33 to E34	Enable upper 32K Enable lower 32K Enable memory power Enable MB64 (battery chip select) Enable Bank-A mode Enable Bank-B mode Set both bank bits the same Strap up used input Select bank bit Reset Bank-A to OFF Reset Bank-B to OFF

^{*} Select bank bit per Section 2.3.2.

Remove U6, U7, U13, U14, U20, U21, U28 and U35 from their sockets. This will disable the top 16K of memory with the help of Magic Mapping.

2.9.6 64K memory with extended addressing

CONNECT	COMMENT									
E17 to E18 E21 to E22 J1-3 to J1-4 J1-5 to J1-6 E35 to E36 E33 to E34 E26 to E27 E29 to E30 *E1 thru E16 E50 to E51 E53 to E54 E56 to E57 E59 to E60	Enable upper 32K Enable lower 32K Enable memory power Enable MB64 (battery chip select) Reset Bank-A LED Reset Bank-B LED Enable extended addressing (A) Enable extended addressing (B) Select extended addressing code Set U28 as RAM Set U21 as RAM Set U14 as RAM Set U7 as RAM									

^{*} See Section 2.2 on Extended Addressing.

2.10 SWO OPTION

Some of the S-100 CPUs, and most of the IEEE 696 CPUs, are equipped with a write status signal called SWO. This signal can be used by the MB64 to control memory writing operations. If your CPU doesn't have this signal or the timing on this line is not correct, the SWO option can be disabled. Be sure to check your CPU for SWO (bus pin 97) and select the appropriate mode.

- Enable SWO for writing: Connect E24 to E25.
- Disable SWO for writing: Connect E23 to E24.

RECOMMENDED SETTING

Mode1	CPU	Manufacturer	Connect					
CB1A CB2 SCC ZPU ZPB - SBC-100 ZPU	80 80 Z-80 Z-80 Z-80 Z-80 Z-80 Z-80 Z-80 Z-80	SSM SSM Cromemco Cromemco Northstar Dynabyte WAMECO SD Systems TDL	E24 to E25 E24 to E25 E24 to E25 E24 to E25 E23 to E24 E23 to E24 E24 to E25 E23 to E24 E24 to E25					

		,
·		

3.0 THEORY OF OPERATION

3.1 32K MEMORY SELECT PROM

The selection of 32K bytes of memory is controlled by a 256 x 4 PROM which replaces several discrete logic ICs by acting as a memory-mapped truth table of the logic functions desired. The address lines and chip select pins of the PROM are used as inputs to the logic function, while the output pins equal the truth table solution.

The input PROM signals are as follows:

```
SOUT [bus 45] = PROM chip select 1 (E1)
BANK-A ENABLE
                      = PROM, address A7
BANK-B ENABLE
                                      A6
NOT ENABLE-A
                                11
                                      A5
                      = !!
                                11
NOT ENABLE-B
                                      Α4
                        * *
                                11
MAGIC MAPPING
                                      A3
                     = 11
                                11
SMEMR [bus pin 47]
                                      A2
PHANTOM [bus pin 67] = "
                                **
                                      Α1
PDBIN [bus pin 78] =
                        11
                                      A0
```

SINP [bus 46] = PROM chip select 2 (E2)

BANK-A or BANK-B ENABLE must be at a logic one to activate 32K of memory on the MB64. The NOT ENABLE lines are used to select the lower or upper 32K block of memory within a 64K boundary. The Magic Mapping line must be a logic one to enable a memory read. The PHANTOM line (per the proposed IEEE 696 standard) must be a logic one to **read** from or **write** into memory.

The output PROM signals are as follows:

```
32K SELECT-A = PROM data 3

32K SELECT-B = " 2

OUTPUT ENABLE = " 1

READ ENABLE = " 0
```

The 32K SELECT lines from the PROM are used to control a 4-to-16 decoder which drives sixteen 2K RAM chips. The OUTPUT ENABLE line from the PROM goes to the $\overline{\text{OE}}$ pin on each RAM. The READ ENABLE line from the PROM controls a tri-state buffer to transfer data from the selected memory chip to the data input (DI) bus in the computer.

To select a 32K block of memory, we need BANK ENABLE and ADDRESS (NOT ENABLE); therefore:

```
32K BLOCK-A = BANK-A ENABLE and not NOT ENABLE-A
= A7 \cdot \overline{A5}
32K BLOCK-B = BANK-B ENABLE and not NOT ENABLE-B
= A6 \cdot \overline{A4}
```

To select one 32K block that does not conflict with the other 32K block, both conditions **MUST NOT** be true. Also, PHANTOM disable must be true to select anything.

32K SELECT-A (D3) = 32K BLOCK-A and not 32K BLOCK-B and PHANTOM = $A7 \cdot \overline{A5} \cdot (\overline{A6} \cdot \overline{A4}) \cdot A1$

32K SELECT-B (D2) = 32K BLOCK-B and not 32K BLOCK-A and PHANTOM = $A6 \cdot A4 \cdot (A7 \cdot \overline{A5}) \cdot A1$

To provide an OUTPUT ENABLE signal to the RAMs, first the CPU must be performing a memory fetch operation (SMEMR) and the 32K must be selected.

OUTPUT ENABLE (D1) = SMEMR and (32K BLOCK-A or 32K BLOCK-B) = $A2 \cdot (A7 \cdot \overline{A5}) \oplus (A6 \cdot \overline{A4})$

To turn on the tri-state buffer (U43) to read memory, the read strobe (PDBIN) from the CPU must be true, as well as the Magic Mapping control line.

READ ENABLE (DO) = PDBIN and SMEMR and MAGIC and PHANTOM and (32K BLOCK-A or 32K BLOCK-B)

= $A0 \cdot A2 \cdot A3 \cdot (A7 \cdot \overline{A5}) \oplus (A6 \cdot \overline{A4}) \cdot A1$

With these four equations for the data lines of the PROM, the following truth table can now be generated for the PROM.

TRUTH TABLE

ADDRESS (Hex)	A7 A6 A5 A4 A3 A2 A1 A0 D3 D2 D1 D0	DATA (Hex)	COMMENT
0 1 2 3 4 5 6 7 8 9 A B C D E F	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	F F F F F F F F F F	No condition met
10 11 12 13 14 15 16 17 18 19 1A 1B 1C 1D 1E 1F	0 0 0 1	F F F F F F F F F F F F F	
20 21 22 23 24 25 26 27 28 29 2A 2B 2C 2D 2E	0 0 1 0 0 0 0 0 0 0 1	F F F F F F F F F F F F F F F F F F F	

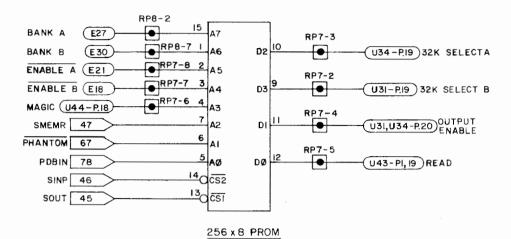
ADDRESS (Hex	A 7	A6	A 5	A 4	A 3	A2	A1	A 0	D 3	D2	D1	DO	DATA (Hex)	COMMENT
30	0	0	1	1	0	0	0	0	1	1	1	1	F	
31	0	0	1	1	0	0	0	1	1	1	1	1	\mathbf{F}	
32	0	0	1	1	0	0	1	0	1	1	1	1	\mathbf{F}	
33	0	0	1	1	0	0	1	1	1	1	1	1	F	
34	0	0	1	1	0	1	0	0	1	1	1	1	\mathbf{F}	
3 5	0	0	1	1	0	1	0	1	1	1	1	1	\mathbf{F}	
36	0	0	1	1	0	1	1	0	1	1	1	1	\mathbf{F}	
37	0	0	1	1	0	1	1	1	1	1	1	1	\mathbf{F}	
38	0	0	1	1	1	0	0	0	1	1	1	1	F	
39	0	0	1	1	1	0	0	1	1	1	1	1	F	
3A	0	0	1	1	1	0	1	0	1	1	1	1	F	
3 B	0	0	1	1	1	0	1	1	1	1	1	1	F	
3C	0	0	1	1	1	1	0	0	1	1	1	1	F	
3D	0	0	1	1	1	1	0	1	1	1	1	1	F	
3E	0	0	1	1	1	1	1	0	1	1	1	1	F	
3F	0	0	1	1	1	1	1	1	1	1	1	1	F	
40	0	1	0	0	0	0	0	0	1	1	1	1	F	
41	0	1	0	0	0	0	0	1	1	1	1	1	F	
42 43	0	1	0	0	0	0	1	0	1	0	1	1	В	Write Block-B
	0	1	0	0	0	0	1	1	1	0	1	1	В	Write Block-B
44 45	0	1	0	0	0	1	0	0 1	1	1	0	1	D	
45 46	0	1	0	0	0	1 1	0 1	0	1	1	0	1	D	D 1 4 1 D
46 47	0	1 1	0	0	0	1	1	1	1 1	0	0	1 1	9 9	Ready to read B
48	0	1	0	0	1	0	0	0	1	1	1	1	F	Ready to read B
49	0	1	0	0	1	0	0	1	1	1	1	1	F	
4A	0	ī	0	0	1	0	1	0	1	0	1	1	В	Write Block-B
4B	0	1	0	0	1	0	1	1	1	0	1	1	В	Write Block-B
4C	0	1	0	0	1	1	0	0	1	1	0	1	D	WILL DIOCK D
4D	0	1	0	0	1	1	0	1	1	ī	0	1	D	
4E	0	1	0	0	1	1	1	0	1	0	0	1	9	Ready to read B
4F	0	1	0	0	Î	ĺ	1	1	1	0	0	0	8	Read Block-B
50	0	1	0	1	0	0	0	0	1	1	1	1	F	
51	0	1	0	1	0	0	0	1	1	1	1		\mathbf{F}	
52	0		0	1		0	1	0	1	1	1	1 1	F	
53	0		0	1				1	1	1	1	1	F	
54	0		0	1				0	1	1	1	1	\mathbf{F}	
55	0		0	1				1		1	1	1	F	
56	0							0		1	1	1	F	
57								1		1	1	1	\mathbf{F}	
58			0					0		1	1	1	F	
59				1				1		1	1	1	F	
5 A								0		1	1	1	F	
5B								1			1	1	F	
5C								0		1	1	1	F	
5D								1			1	1	F	
5E	0					1		0			1	1	F	
5F	0	T	0	1	1	1	1	1	1	1	1	1	F	

ADDRESS (Hex)	A 7	A 6	A 5	∆ 4	A 3	A 2	A1	A 0	D3	D2	D1	DO	DATA (Hex)	COMMENT
60	0	1	1	0	0	0	0	0	1	1	1	1	\mathbf{F}	
61	0	1	1	0	0	0	0	1	1	1	1	1	\mathbf{F}	
62	0	1	1	0	0	0	1	0	1	0	1	1	В	Write Block-B
63	0	1	1	0	0	0	1	1	1	0	1	1	В	Write Block-B
64	0	1	1	0	0	1	0	0	1	1	0	1	D	
65	0	1	1	0	0	1	0	1	1	1	0	1	D	
66	0	1	1	0	0	1	1	0	1	0	0	1	9	Ready to read B
67	0	1	1	0	0	1	1	1	1	0	0	1	9	Ready to read B
68	0	1	1	0	1	0	0	0	1	1	1	1	F	
69	0	1	1	0	1	0	0	1	1	1	1	1	F	
6A 6B	0	1 1	1	0	1	0	1	0	1	0	1	1	В	Write Block-B
6C	0	1	1 1	0	1 1	0 1	1	1	1	0	1	1	В	Write Block-B
6D	0	1	1	0	1	1	0	0 1	1 1	1 1	0	1	D	
6E	0	1	1	0	1	1	1	0	1	0	0	1 1	D	Dander to see I D
6F	0	1	1	0	1	1	1	1	1	0	0	0	9 8	Ready to read B Read Block-B
70	0	1	1	1	0	0	0	0	1	1	1	1	F	
71	0	1	1	1	0	0	0	1	1	1	1	1	\mathbf{F}	
72	0	1	1	1	0	0	1	0	1	1	1	1	F	
73	0	1	1	1	0	0	1	1	1	1	1	1	F	
74	0	1	1	1	0	1	0	0	1	1	1	1	\mathbf{F}	
75 76	0	1	1	1	0	1	0	1	1	1	1	1	F	
76 77	0	1	1	1	0	1	1	0	1	1	1	1	F	
77 70	0	1	1	1	0	1	1	1	1	1	1	1	F	
78 79	0	1 1	1 1	1	1	0	0	0	1	1	1	1	F	
7 9 7 A	0	1	1	1 1	1 1	0	0	1 0	1	1 1	1 1	1	F	
7 B	0	1	1	1	1	0	1 1	1	1 1	1	1	1 1	F	
7 C	0	1	1	1	ĺ	1	0	0	1	1	1	1	F F	
7 D	Ö	1	1	1	1		0	1	1	1	1	1	F	
7E	ŏ	1	1	ī	î	1	1	0	1	î	1	1	F	
7F	0	1	1	1	1	1	1	1	1	1	1	1	F	
80	1	0	0	0	0		0	0	1	1	1	1		
81	1	0	0	0	0		0	1	1	1	1	1	F F	
82	1	0	0	0			1	0	Ô	1	î	1	7	Write Block-A
83	1	0	0	0	0		1	1	Õ	î	1	î	, 7	Write Block A
84	1		0	0	0		0	0	1	1	0	1	D	WIICC BIOCK H
85	1	0	0	0	0		0	1	1	1	0	1	D	
86	1	0	0	0	0	1	1	0	0	1	0	1	5	Ready to read A
87	1	0	0	0	0	1	1	1	0	1	0	1	5	Ready to read A
88	1	0	0	0	1	0	0	0	1	1	1	1	F	
89	1	0	0	0		0	0	1	1	1	1	1	F	
8A	1			0			1	0	0	1	1	1	7	Write Block-A
8B				0			1	1	0	1	1	1	7	Write Block-A
8C				0				0	1	1	0	1	D	
8D				0			0	1			0	1	D	
8E 8F	1 1		0	0		1 1	1 1	0 1	0	1 1	0	1 0	5 4	Ready to read A Read Block-A

ADDRES (Hex)			TA lex) Comment
90 91 92 93 94 95 96 97 98 99 9A 9B 9C 9D 9F	1 0 0 1 0 0 0 0 0 1 1 0 0 0 1 1 0 0 1 0 1 0 1 0 1 0 1 0 1 0 1 1 0 0 1 1 1 1 0 0 1 1 1 1 0 0 1 1 1 0 0 1 1 1 0 0 1 1 1 0 0 1 1 1 0 0 1 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0 1 1 0 0	1 1 1 1 1 1 1 0 1 1 1 1 1 1 1 1 1 1 1 1	F F F T Write Block-A Write Block-A Ready to read A Ready to read A Write Block-A Write Block-A Write Block-A
A0 A1 A2 A3 A4 A5 A6 A7 A8 A9 AA AB AC AD AE	1 0 1 0 0 1 0 0 1 0 1 0 0 1 0 1 1 0 1 0 0 1 1 0 1 0 1 0 0 1 1 0 1 0 1 0 1 0 0 0 1 0 1 0 1 0 0 1 1 0 1 0 1 0 1 0 0	1 1 1 1 F 1 1 1 1 F 1 1 1 1 F 1 1 1 1 F 1 1 1 1	Joek A
B0 B1 B2 B3 B4 B5 B6 B7 B8 B9 BA BB BC BD BE BF	1 0 1 1 0 0 0 0 1 1 1 0 1 1 0 0 0 1 1 1 1 0 1 1 0 0 1 0 1 <td>1 1 1 F 1 1 1 F</td> <td></td>	1 1 1 F 1 1 1 F	

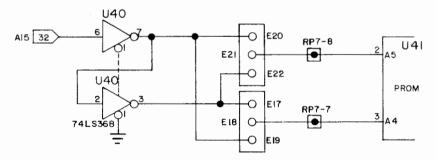
ADDRESS (Hex)	A 7	A 6	A 5	∆ 4	A 3	A2	Al	A 0	D3	3 D	2	D1	D 0	DATA (Hex)	COMMENT
CO	1	1	0	0	0	0	0	0	1	1		1	1	F	
C1	1	1	0	0	0	0	0	1	1	1		1	1	F	
C2	1	1	0	0	0	0	1	0	1	1		1	1	F	
C3	1	1	0	0	0	0	1	1	1	1		1	1	\mathbf{F}	
C4	1	1	0	0	0	1	0	0	1	1		1	1	\mathbf{F}	
C5	1	1	0	0	0	1	0	1	1	1		1	1	\mathbf{F}	
C6	1	1	0	0	0	1	1	0	1	1		1	1	F	
C7	1	1	0	0	0	1	1	1	1	1		1	1	\mathbf{F}	
C8	1	1	0	0	1	0	0	0	1	1		1	1	F	
C9	1	1	0	0	1	0	0	1	1	1		1	1	F	
CA	1	1	0	0	1	0	1	0	1	1		1	1	F	
СВ	1	1	0	0	1	0	0	1	1	1		1	1	F	
CC	1	1	0	0	1	1	0	0	1	1		1	1	F	
CD	1	1	0	0	1	1	0	1	1	1		1	1	F	
CE	1	1	0	0	1	1	1	0	1	1		1	1	F	
CF	1	1	0	0	1	1	1	1	1	1		1	1	F	
DO	1	1	0	1	0	0	0	0	1	1		1	1	F	
D1	1	1	0	1	0	0	0	1	1	1		1	1	F	
D2	1	1	0	1	0	0	1	0	0	1		1	1	7	Write Block-A
D3	1	1	0	1	0	0	1	1	0	1		1	1	7	Write Block-A
D4 D5	1 1	1	0	1	0	1	0	0	1	1		0	1	D	
D6	1	1	0	1	0		0	1	1	1		0	1	D	
D6 D7	1	1	0	1	0	1	1	0	0	1		0	1	5	Ready to read A
D8	1	1	0	1 1		1	1	1	0	1		0	1	5	Ready to read A
D9	1	1		1	_	-	0	0	1	1		1	1	F	
DA	1	1		1		-	0 1	1	1	1		1	1	F	
DB	1	1					1	0 1	0	1]		1	7	Write Block-A
DC	1	1						0	0 1	1 1]		1	7	Write Block-A
DD	1	1					-	1	1	1	()	1	D	
DE	1	1		1				0	0	1	(1 1	D	Decit .
DF	1	1		1		_	1	1	0	1	(0	5 4	Ready to read A Read Block—A
E0	1	1	1	0	0	0	^	0							nead Diock II
E1	1	1					0 0	0	1	1	1		1	F	
E2	1	1						1 0	1 1	1	1		1	F	
E3	1							1	1	0	1		1	В	Write Block-B
E4	1							0	1	1	0		1	В	Write Block-B
E5	1							1	1	1	C		1 1	D	
E6	1							0	1	0	0		1	D	D 1
E7	1							1	1	0	0		1	9	Ready to read B
E8								0	1	1	1		1	9	Ready to read B
E9								1	1	1	1		1	F	
EA								0	1	0	1		1	F	Unite Di i D
EB								1		0	1		1	В	Write Block-B
EC								0	1	1	0		1	B D	Write Block-B
ED								1		1	0		1	D	
EE								0		0	0		1	р 9	Dondy to mad D
EF								1		0	0		0	8	Ready to read B Read Block-B

ADDRESS													DATA	
(Hex)	A 7	A6	A 5	A 4	A3	A2	Al	AO	D3	D2	D1	DO	(Hex)	COMMENT
F0	1	1	1	1	0	0	0	0	1	1	1	1	F	
F1	1	1	1	1	0	0	0	1	1	1	1	1	F	
F2	1	1	1	1	0	0	1	0	1	1	1	1	F	
F3	1	1	1	1	0	0	1	1	1	1	1	ī	F	
F4	1	1	1	1	0	1	0	0	1	1	1	1	F	
F5	1	1	1	1	0	1	0	1	1	1	1	1	F	
F6	1	1	1	1	0	1	1	0	1	1	1	1	F	
F 7	1	1	1	1	0	1	1	1	1	1	1	1	F	
F8	1	1	1	1	1	0	0	0	1	1	1	1	F	
F9	1	1	1	1	1	0	0	1	1	1	ī	1	F	
FA	1	1	1	1	1	0	1	0	1	1	1	ī	F	
FB	1	1	1	1	1	0	1	1	1	1	1	1	F	
FC	1	1	1	1	1	1	0	0	1	1	1	$\bar{1}$	F	
FD	1	1	1	1	1	1	0	1	1	1	1	1	F	
FE	1	1	1	1	1	1	1	0	1	1	1	1	F	
\mathbf{FF}	1	1	1	1	1	1	1	1	1	1	1	1	F	



3.2 MEMORY ADDRESS SELECT

Memory address selection is provided by jumpers E17 thru E22. These jumpers allow the user to select the lower or upper 32K of memory within a 64K boundary by selecting the normal or inverted state of the A15 bus line. The input pins A4 & A5 must be a logic zero to enable 32K of memory.

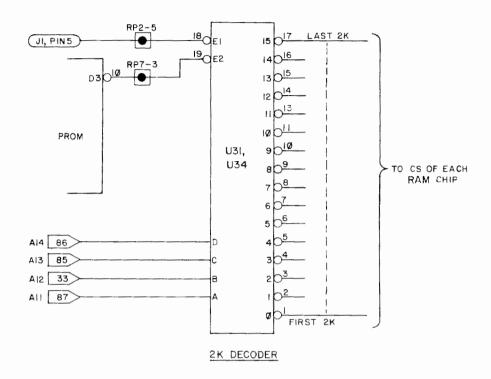


MEMORY ADDRESS SELECT

3.3 2K MEMORY DECODE

After the input conditions are met on the PROM per Section 3.1, one of the two 32K select lines (D3 or D2) goes low, enabling a 4-to-16 decoder IC (74LS154). The 4-to-16 decoder receives address lines All thru Al4 as its input and therefore will decode down to every 2K memory increment within one 32K boundary. Each of the 16 outputs of the 74LS154 goes to the chip select pin of a memory IC within a memory block.

The 4-to-16 decoder has two enabling pins. While one enable pin goes to 32K Select, the other enable pin goes to the battery back-up connector Jl. Jl, pin 5, is used by the battery back-up option to protect the data within RAM from being changed while on battery power. Without battery back-up, this pin is normally grounded to enable the 4-to-16 decoder.



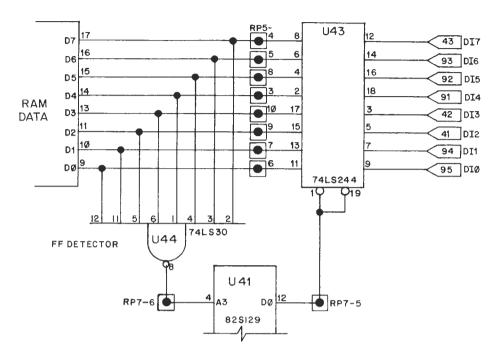
3.4 MAGIC MAPPING

Originally incorporated into the MB8A in 1977, the Magic Mapping circuit allows a socket on the memory board and its supporting circuitry to be disabled by simply removing the IC chip. The Magic Mapping circuit disables the tri-state buffer from driving the data input (DI) bus if the memory IC is removed. Memory space (in 2K increments) can be made available for memory mapped video, I/O, disks or ROM boards within the 64K of memory.

Magic Mapping relies on the **assumption** that the master CPU board has external pull-up resistors on the DI lines or the computer system has a **terminated bus.** The pull-up resistors on the DI bus will force the bus to "FF" Hex state, even if no S-100 board is present. Therefore, "FF" does not have to be transferred from the memory board to the DI bus.

U44 (74LS30) is an "FF" detector on the MB64. If an addressed memory chip puts out any Hex code except FF, then U44 outputs a one which will enable the read buffer (U43). If "FF" is detectd, the output tri-state buffer is turned off, allowing any external S-100 board to drive the DI bus.

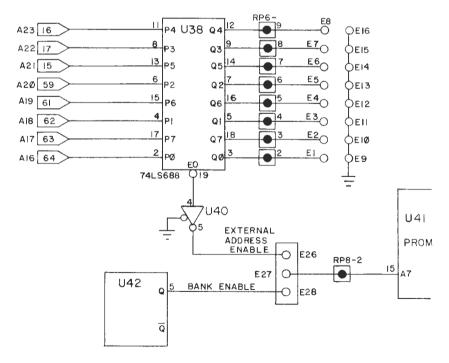
Magic Mapping allows for an entire 2K memory increment to be available for other memory boards or smaller areas by filling selected areas of RAM with "FF" Hex.



MAGIC MAPPING CIRCUIT

3.5 EXTENDED ADDRESSING

The proposed IEEE 696 standard for the S-100 bus has added 8 additional address lines, A16 thru A23, for up to 16 megabytes of memory. The MB64 has an on-board 8-bit comparator (U38) which can be set to enable/disable the memory per the state of the extended address lines. Input lines A6 & A7 of U41 (PROM) are used to enable or disable a 32K block of memory per the equations in Section 3.1.

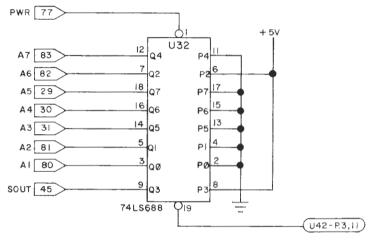


EXTENDED ADDRESS DECODER

3.6 BANK SELECT CIRCUIT

The bank select function is driven by I/O port 40 or 41 Hex. This function is used in memory management schemes to provide multiple layers of memory, all addressed at the **SAME** address space. Each banked memory board is turned on or off by the memory manager software, for each task to be executed, as scheduled under time or priority interrupts.

The I/O address decoder is one 74LS688 (U32) comparator. This IC puts out a negative pulse every time PWR, SOUT, and Al thru A7 match the preset inputs on the other side of this comparator. Due to the lack of sufficient inputs to U32, AO was not sensed, so the bank port address is 40 Hex and 41 Hex.

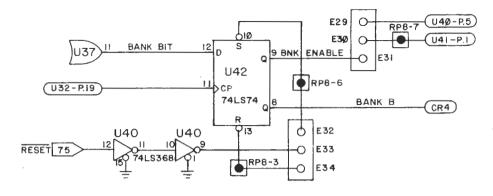


I/O ADDRESS DECODER

The bank select circuit is divided into two banks of 32K each. A bit within the byte sent to I/O port 40 Hex controls the activation of a bank. To save the user-selected bit for continuous bank control, a flip-flop (U41) is used for storage. The bit to be stored is selected by a 16-pin IC header. If the bit sent to the D-input of the flip-flop is a one, then the 32K block is enabled. If the bit sent is a zero, then 32K is disabled.

On power up in a bank-selected computer system, one memory bank is usually activated as the master. The flip-flop has been provided with jumper options to force the 32K block ON or OFF on power-up (POC) or reset. [NOTE: The proposed IEEE 696 standard requires Reset to be generated when the POC bus line is low.]

Jumpering E32 to E34 (E35 to E37) connects the computer's reset signal to the set input or clear input of the bank flip-flop.



BANK FLIP-FLOP

If jumper E32 to E33 (or E36 to E37) is connected, the memory block that flip-flop is controlling becomes a master bank on reset. If jumper E33 to E34 (or E35 to E36) is connected, the reset signal clears the "Q" output of the flip-flop and that memory block.

Two bank select indicators are provided on the MB64. Each flip-flop drives a LED to indicate if one of the 32K bank flip-flops are enabled.

3.7 BATTERY BACKUP

The MB64 is provided with a connector labelled Jl for an optional battery backup circuit. This battery option can maintain power to the memory chips for more than 5 hours, depending on the memory type and manufacturer used. For further information, please contact SSM for features and date of availability.

3.8 BUS INTERFACE

The MB64's memory chips are isolated from the S-100 bus by buffer ICs (74LS244, 74LS125, etc.) or general logic (74LS154, 82S129, etc.).

- a. Address lines AO thru A7 are buffered by U33 (74LS244).
- b. Address lines A8 thru A10 are buffered by U39 (74LS244).
- c. Address lines All thru Al4 are isolated by U31 & U34 (74LS154).
- d. Address line Al5 is isolated by U40 (74LS368).
- e. Address lines Al6 thru A23 are buffered by U38 (74LS688).
- f. Status lines SINP and SOUT are isolated by U41 (82S129).
- g. The status line for memory read (SMEMR) is isolated by U41 (82S129).
- h. The read strobe (PDBIN) is isolated by U41 (82S129).
- i. The write strobe (\overline{PWR}) is isolated by U32 & U39 (74LS688 & 74LS125).
- j. The read/write disable line (Phantom) is isolated by U4 (82S129).
- k. The status line for writing (SWO) is isolated by U39 (74LS125).
- The memory data is read via U43 (74LS244).
- m. The memory data is written via U45 (74LS244).

The data buffer used during a read operation (U43) is controlled by the logic truth table within U41 (82S129) and issued on pin 12. U41, pin 12 will not provide a chip enable to U43 until the SMEMR, PDBIN, PHANTOM, A15, SINP and SOUT signals are in the correct state (see Section 3.1).

The data buffer used during a write operation (U45) is controlled by the buffer gate U39 (74LS125). To guarantee that the data is still present on the memory chip when the $\overline{\text{WE}}$ signal goes high, the write line (U39, pin 11) drives the RAM and U45 directly. (U45 provides 10 nanoseconds or greater delay before the data becomes invalid at the end of a write cycle which meets the manufacturer's specification of 0 nanoseconds of data hold time.)

4.0 MEMORY TEST PROGRAM

```
;
                       Simple Memory Test
                       Written by Andrew Schneider
                       Modified by Malcolm Wright
                ;
                       Coyright 1977 by SSM
                       Set "START" to the starting address of
                       memory to be tested. Set "MEND" to the last
                       address of memory to be checked.
                ;
                       The program will stop (HALT) when complete
                       or if an error was found. "GORB" (good or
                ;
               ;
                       bad) will be set to 00H for good memory or
                       to the byte pattern that would not read or
                ;
                       write correctly into memory. "LAST" is the
                       location where the last address tested will
                       be saved. If memory is good, then LAST=MEND.
= 0008
               BEGIN
                      EQU
                               0008
                                         ;Start of program
E000 =
               START
                       EOU
                               H0000
                                         ;Beginning of address
E3FF =
               MEND
                       EQU
                                         ;Ending address
                               7 F F F H
8000
                               BEGIN
                       ORG
8000 210000
                       LXI
                               H, START
8003 11FF7F
                       LXI
                               D, MEND
8006 2B
                       DCX
                               Η
8007 23
               LOOP:
                       INX
                               Η
8008 3E7F
                       MVI
                               A,7FH
800A 07
               CHECK: RLC
800B 77
                       MOV
                               M,A
800C BE
                       CMP
                               M
800D C22080
                       JNZ
                               ERROR
8010 B7
                       ORA
                               Α
8011 FA0A80
                       JM
                               CHECK
8014 7B
                       MOV
                               A,E
8015 BD
                       CMP
8016 C20780
                       JNZ
                               LOOP
8019 7A
                       MOV
                               A,D
801A BC
                       CMP
                               Н
801B C20780
                       JNZ
                               LOOP
801E 3E00
                       MVI
                               A,0
8020 322780
               ERROR: STA
                               GORB
                                         ; If using an IMSAI front panel
                                                             CMA
                                         replace with
                                                             OUT
                                                                 0FFH
                                         ;to display byte on front panel.
8023 222880
                       SHLD
                               LAST
8026 76
                       HLT
8027 00
               GORB:
                       DB
                               0
8028 0000
                               0
               LAST:
                       DW
802A
                       END
```

5.0 TROUBLESHOOTING

Some checkout of the MB64 can be done by just watching the LEDs on the board.

5.1 BANK SELECT TEST

If you have another memory board which will run your system, you can temporarily disable the MB64 to test the banking circuitry.

- a. Remove jumpers from E17 to E22.
- b. Make a test header for E38 to E48.

```
Connect E40 to E48 (Bit0)
Connect E39 to E47 (Bit1)
Connect E38 to E46 (Bit2)
```

c. Run the following routine (clear BANKS):

```
ORG 100H

100 AF XRA A ; SET BANK BYTE=0

101 D3,40 OUT 40H ; SEND BYTE

103 C3,00,00 JMP 0 ; GO BACK TO CP/M
```

All LEDs of the MB64 should not be lit. This checks both halves of U42 for a zero.

d. Now run:

```
ORG 100H

100 3E,01 MVI A,1 ; SET BANK BYTE=1

102 D3,40 OUT 40H ; SEND BYTE

104 C3,00,00 JMP 0 ; GO BACK TO CP/M
```

Only the LED labelled BNKA should be lit. This checks one-half of U42.

e. Now run:

```
ORG 100H

100 3E,02 MVI A,2 ; SET BANK BYTE=2

102 D3,40 OUT 40H ; SEND BYTE

104 C3,00,00 JMP 0 ; GO BACK TO CP/M
```

Only the LED labelled BNKB should be lit. This checks the other half of U42 and one input of U37.

f. Now run:

```
ORG 100H

100 3E,04 MVI A,4 ; SET BANK BYTE=4

102 D3,40 OUT 40H ; SEND BYTE

104 C3,00,00 JMP 0 ; GO BACK TO CP/M
```

Only the LED labelled BNKB should be lit. The checks the other input of U37.

g. Last, run:

ORG 100H ; SELECT UNUSED BANK
100 3E,08 MVI A,8 ; SET BANK BYTE=8
102 D3,40 OUT 40H ; SEND BYTE
104 C3,00,00 JMP 0 ; GO BACK TO CP/M

No LEDs on the MB64 should be lit.

5.2 BANK PRESET

If you have another memory board which will run your system, you can temporarily disable the MB64 to test the banking circuitry.

- a. Remove jumpers from E17 to E22.
- b. Install jumpers E35 to E36 and E33 to E34.
- c. Push computer Reset. (DON'T LET THE SYSTEM BOOT.)

No LEDs on the MB64 should be lit. This tests the reset inputs of U42.

- d. Install jumpers at E36 to E37 and E32 to E33 now.
- e. Push computer Reset.

Both LEDs on the MB64 labelled BNKA & BNKB should be lit. This tests the set inputs of U42.

- f. Install jumpers at E36 to E37 and E33 to E34.
- g. Push computer Reset.

One LED on the MB64 labelled BNKA should be lit. This tests that the set/reset inputs are not shorted between the halves of U42.

5.3 MEMORY ADDRESSING

If the MB64 is set up in one of the many standard configurations indicated in Section 2.9, the LED's ENA or ENB should be flashing dimly as the computer accesses the board. If there are no jumpers on E17 thru E22, the MB64 cannot be read.

By enabling half of the MB64 (32K), it should be possible to run user-defined memory tests. Jumper E18 to E19 to test memory block B as the first 32K and leave E21 open. Jumper E21 to E22 to test memory block A as the first 32K and leave E18 open.

6.0 WARRANTY

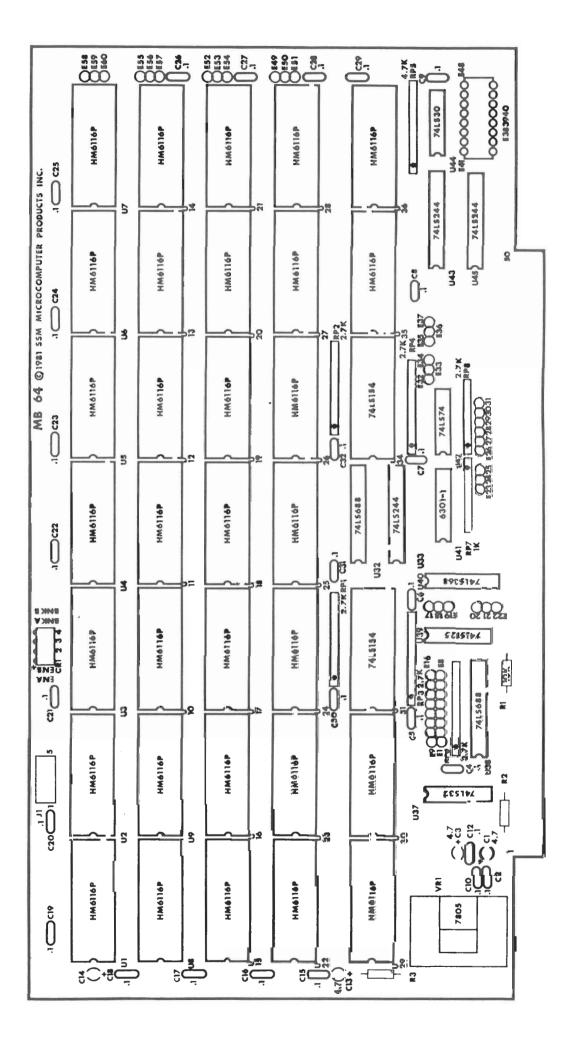
SSM Microcomputer Products, Inc. warrants its products to be free from defects in materials and/or workmanship for a period of ninety (90) days for kits and one (1) year for factory assembled boards. In the event of malfunction or other indication of failure attributable directly to faulty workmanship and/or material, then, upon return of the product (postage paid) to SSM at 2190 Paragon Drive, San Jose, CA 95131, "Attention: Warranty Claims Department", SSM will, at its option, repair or replace the defective part or parts to restore said product to proper operating condition. All such repairs and/or replacements shall be rendered by SSM without charge for parts or labor when the product is returned within the specified period of the date of purchase. This warranty applies only to the original purchaser.

This warranty will not cover the failure of SSM products which at the discretion of SSM shall have resulted from accident, abuse, negligence, alteration, or misapplication of the product. While every effort has been made to provide clear and accurate technical information on the application of SSM products, SSM assumes no liability in any events which may arise from the use of said technical information.

This warranty is in lieu of all other warranties, expressed or implied, including warranties of mercantability and fitness for use. In no event will SSM be liable for incidental and consequential damages arising from or in any way connected with the use of its products. Some states do not allow the exclusion or limitation of incidental or consequential damages, so the above limitation or exclusion may not apply to you.

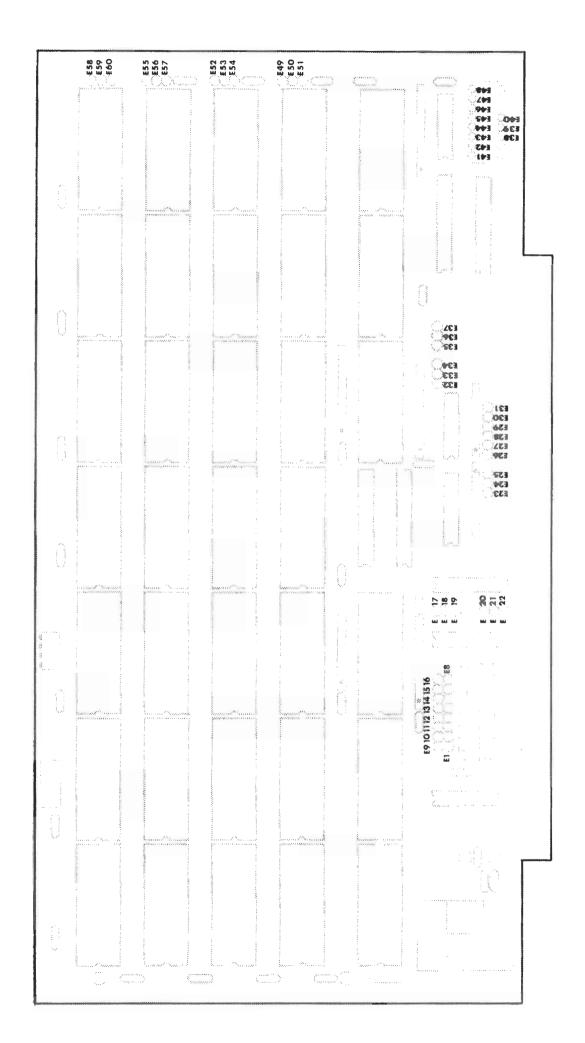
IMPORTANT: Proof of purchase is necessary for products returned for repair under warranty. Before returning any product, please call our Customer Service Department for a return authorization number.

		j



ASSEMBLY DRAWING

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JUMPER DRAWING

© 1981 SSM "icrocomputer Products, Inc. All Right! sserved

AØ THRU AIS = CHIPS IN BLOCK A BØ THRU BIS = CHIPS IN BLOCK B

A4 A14 A8 B2 B3 B10 B15 +2000 +7000 +4000 +1000 +1800 +5000 +7800 A3 A13 A11 B0 B4 B9 B14 +1800 +5800 +2000 +2000 +7800 +7800 +7800 A1 A7 A6 A10 B5 B7 B12 +0000 +3800 +3800 +5800 +6600 A0 A5 B6 B7 B1 +9000 +2800 +5800 +6600 A0 A5 A500 +6600	AI4	(mana)							Section 2
A13 A11 B0 B4 B9 H800 +5000 +2000 +5000 H800 +5000 H800 H800 +2000 H800 H800 H800 H800 H800 H800 H800	-2000 +7000 +1000 +1800 +5000 A3 A13 A11 B0 B4 B9 +1800 +5800 +5800 +4800 +4800 A2 A15 A12 A9 B6 B8 +1000 +7800 +5000 +3000 +4000 +4000 +4000 A0 A5 A6 A500 +2800 +3800 +5800 +5800 A0 A5 A5 A5 B11 +5800 +5800 A0 A5 A6 A5 B11 +5800 A0 A5 A6 A5 A6 A5800	A4	A14	Α8	B2	B3		BIØ	
AIS AII BØ B4 B9 +6800 +2000 +2000 +2000 +4800 AIS AIZ A9 B6 B8 +4000 +3000 +3000 +4000 +4000 A7 A6 AIØ B5 B7 A7 A6 AIØ B5 B7 A5 A6 A10 B5 B7 +2800 +3000 +5000 +5000 +5800	A2 A13 A11 B0 B4 B9 +18000 +20000 +20000 +48000 +48000 A2 A15 A12 A9 B6 B8 +10000 +78000 +30000 +28000 +38000 +40000 +28000 A0 A5	+2000	+7000	+4000	+1000	+1800		+5000	Yearne A
46800 +5800 +6000 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +4800 +5800 -5800 +5800 -5800 <td< td=""><td>A2 A15 A12 A9 B6 B8 B6 B8 H0000 +2000 +4000 +4800 +4800 +4800 +4800 +4800 +4800 +4000 +4000 +4000 +4000 +4000 +4000 +4000 +4000 +500</td><td>A3</td><td>AI3</td><td>All</td><td>. 0A</td><td>, 84</td><td></td><td>89</td><td>B14</td></td<>	A2 A15 A12 A9 B6 B8 B6 B8 H0000 +2000 +4000 +4800 +4800 +4800 +4800 +4800 +4800 +4000 +4000 +4000 +4000 +4000 +4000 +4000 +4000 +500	A3	AI3	All	. 0A	, 84		89	B14
AIS AI2 A9 B6 B8 +7800 +6000 +4800 +3000 +4000 10 +3800 +3800 +3800 +3800 10 +2800 +2800 +5800	AC AIS AI2 A9 B6 B8 +10000 +7800 +4800 +4800 +4800 44000	+1800	+6800	+5800	0000+	+500		+ 4800	+7000
1 +7800 +6000 +4800 +4800 +40	AI A7 A6 H800 +4800 +4800 +4000 H9000 H90000 H90	A2	AIS	A12	A 9	:		88	BI3
A7 A6 A10 B5 B7 +3800 +5000 +2800 +3800 +2800 +5800 +5800	A0 A5 H2800 +5000 +2800 +2800 +3800 +5800 +5800 +5800 H5800 H5800	+1000	+7800	+6000	+4800	+3002	· ·	+4000	+6800
+3800 +5000 +5000 +2800 +5800 +5800 +5800 +5800	40800 +3800 +5800 +3800 A0 A5 BII +0000 +2800 +5800 -0FFSET ADDRESS FROM STAND OF A 2017 ADDRESS	ΑΙ	A7		AIØ	98		87	BI2
H28000 +58000 +58000 -58000 -58000 -58000 -58000 -58000 -58000 -58000 -58000 -58000 -58000 -58000 -580	A@ A5	+ Ø8ØØ	+3800		+5000	+2800	R	+3800	+6000
H2800 +5800	### ### ### ### ### ### ### ### #### ####					 			
+2800	+øøøø +28øø +58øø OFFSET ADDRESS FROM		0000000				:	B =	00.110000000000000000000000000000000000
	OFFSET ADDRESS FROM	+0000	1)	Salas Amerikan K			+5800	00000
	OFFSET ADDRESS FROM			**************************************					
	OFFSET ADDRESS								
	OFFSET ADDRESS								

MEMORY MAP

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PARTS LIST

IC	8	8
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32	U1-U30, 35, 36	HM6116P	2K x 8 CMOS static RAM (150 ns)
2	U31, 34	74LS154	
2	U32, 38	74LS688	8-bit comparator
3	U33, 43, 45	74LS244	·
1	U39	74LS125	
1	U40	74LS368	
1	U41	82S129	256 x 4 bipolar PROM (marked MB64-LE)
1	U42	74LS74	•
1	U44	74LS30	
1	U37	74LS32	
1	VR1	7 80 5	+5V voltage regulator

RESISTORS

1	Rl	10K ohm 1/4W 5% (brown, black, orange)
5	RP1, 2, 3, 4, 6	2.7K ohm 10-pin SIP resistor network
1	RP5	4.7K ohm 10-pin SIP resistor network
1	RP8	2.7K ohm 8-pin SIP resistor network
1	RP7	1K ohm 8-pin SIP resistor network

CAPACITORS

4	C1, 3, 13, 14	4.7 uf DIP tantalum
27	2, 4-10, 12, 15-32	.1 uf monolithic capacitor

DIODES

4 CR1-4

LED Dialight 555-2007

SOCKE	ETS	CONNECTORS	
4	14-pin sockets	9 3 x 1 header strips	3
3	16-pin sockets	1 6 x 1 header strip	
5	20-pin sockets	1 5 x 2 header strip	
34	24-pin sockets	1 8 x 2 header strip	

HARDWARE

1	#6 hardware set
1	Small heatsink
2	Card ejectors
19	Mini-jumpers
1	MB64 PC board
1	MB64 manual
1	Warranty card
1	16-pin IC header



HITACHI SERIES HM6116P

2048 X 8 BIT HIGH SPEED STATIC C MOS RAM

@HITACHI

■ FEATURES

• Single 5V Supply and High Density 24 Pin Package

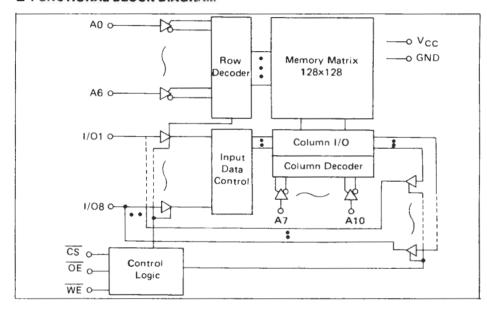
High Speed: Fast Access Time
 Low Power Standby and
 Low Power Operation:
 120ns/150ns/200ns max.
 100μW typ. (Standby)
 180mW typ. (Operation)

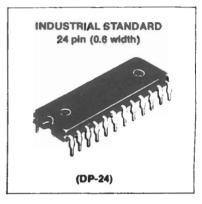
Directly TTL Compatible All Input and Output

Pin Out Compatible with Standard 16K EPROM/MASK ROM

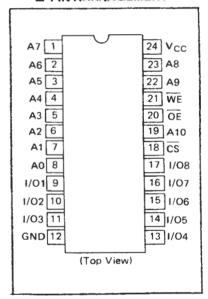
• Equal Access and Cycle Time

E FUNCTIONAL BLOCK DIAGRAM





■ PIN ARRANGEMENT



■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to GND	V _{IN}	-0.5 to 7.0	V
Operating Temperature	Topr	0 to 70	°C
Storage Temperature	Tsig	-55 to 125	°C
Temperature Under Bias	Tbias	-10 to 85	°C
Power Dissipation	P_T	1.0	W

TRUTH TABLE

CS	OE	WE	Mode	V _∞ Current	I/O Pin	Ref. Cycle
Н	Х	Х	Not Selected	I _{SB} , I _{SBI}	High Z	
L	L	Н	Read	I _{cc}	Dout	Read Cycle No. 1 ~ 3
L	Н	L	Write	I _{cc}	Din	Write Cycle No. 1
L	L	L	Write	I _{cc}	Din	Write Cycle No. 2

■ RECOMMENDED DC OPERATING CONDITIONS (0° C \leq Ta \leq 70°C)

Parameter	Symbol	Min	Тур	Max	Unit	Notes
Supply Voltage	V_{cc}	4.5	5.0	5.5	V	
Supply Voltage	GND	0	0	0	V	
Input High (logic I) Voltage	V _{IH}	2.2	3.5	6.0	V	
Input Low (logic 0) Voltage	V_{IL}	*-1.0		0.8	V	*Pulse width: 50ns DC: V11. min = 0.3V

■ DC AND OPERATING CHARACTERISTICS ($0^{\circ}C \le Ta \le 70^{\circ}C$, $V_{cc} = 5V \pm 10\%$, GND = 0V)

Parameter	Symbol	HM6116P-2			HM6116P-3/P-4				70 . 60 . 101	
		Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions	Notes
Input Leakage Current	$ I_{II} $		I	10		1	10	μА	V_{CC} = MAX V_{IN} = GND to V_{CC}	
Output Leakage Current	11.0			10			10	μА	$CS = V_{IH} \text{ or } OE = V_{IH}$ $V_{I:O} = GND \text{ to } V_{CC}$	
Operating Power Supply Current: DC	I_{CC}		40	80		35	70	mA	$CS = V_{H,i}$ $I_{I \cap O} = 0 \text{mA}$	
Operating Power Supply Current: DC	Icci		35			30		mA	$V_{IH} = 3.5 \text{V}, V_{II} = 0.6 \text{V}$ $I_{I=0} = 0 \text{mA}$	2
Average Operating Current ²	I_{CC2}		40	80		35	70	mA	MIN cycle duty = 100%	
Standby Power Supply Current: DC	I_{SB}		5	15		5	15	mA	CS = V _{IH}	
Standby Power Supply Current: DC	I_{SBI}		0.02	2		0.02	2	mA	$CS \ge V_{CC} - 0.2V$ $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$	
Output Low Voltage	V_{OI}			*0.4			**0.4	V	$*I_{OI} = 4\text{mA}$ $**I_{OL} = 2.1\text{mA}$	3
Output High Voltage	V_{OH}	2.4			2.4				$I_{OL} = 1.0 \text{mA}$	

NOTES: 1. Typical limits are at $V_{CC} = 5.0V$, $Ta \approx +25^{\circ}C$ and specified loading

2. Reference Only.

3. HM6116P-2: I_{OL} = 4.0mA, HM6116P-3/HM6116P-4: I_{OL} = 2.1mA

■ CAPACITANCE $(Ta = 25^{\circ}C, f = 1.0 \text{ MHz})^{\dagger}$

Parameter	Symbol	Тур	Max	Unit	Conditions	Notes
Input Capacitance	C_{IV}	3	5	pF	$V_{IN} = 0V$	
Input Output Capacitance	C_{I^*O}	5	7	pF	$V_{IO} = 0V$	

NOTE: 1. This parameter is sampled and not 100% tested.

. AC TEST CONDITIONS

Input pulse levels:	0.8V to 2.4V
Input rise and fall times:	10 ns
Input and output timing reference levels:	1.5V
Output load:	1 TTL Gate and $C_L = 100pF$

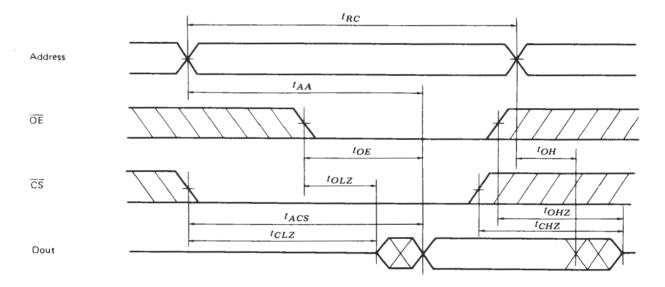
(Including scope & jig)

■ AC CHARACTERISTICS (Ta = 0°C to 70°C, V_{cc} = 5V ± 10% unless otherwise noted.)

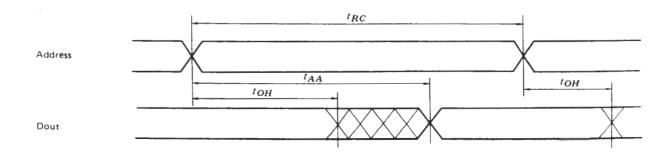
• READ CYCLE

_	Symbol	HM6116P-2		HM6116P-3		HM6116P-4		
Parameter		Min	Max	Min	Max	Min	Max	Unit
Read Cycle Time	1 _{RC}	120		150		200		ns
Address Access Time	t_{AA}		120		150		200	ns
Chip Select Access Time	tacs		120		150		200	ns
Chip Selection to Output in Low Z	t _{CLZ}	10		15		15		ns
Output Enable to Output Valid	toE		80		100		120	ns
Output Enable to Output in Low Z	tolz	10		15		15		ns
Chip Deselection to Output in High Z	1 _{CHZ}	0	40	0	50	0	60	ns
Output Disable to Output in High Z	tonz	0	40	0	50	0	60	ns
Output Hold from Address Change	toн	10		15		15		ns

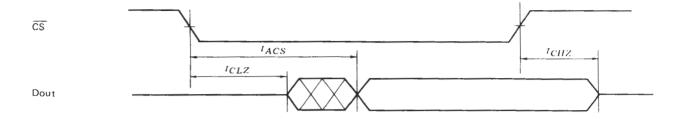
■ TIMING WAVEFORM OF READ CYCLE NO. 11,5



■ TIMING WAVEFORM OF READ CYCLE NO. 21, 2, 4, 5



■ TIMING WAVEFORM OF READ CYCLE NO. 3^{1, 3, 4, 5}

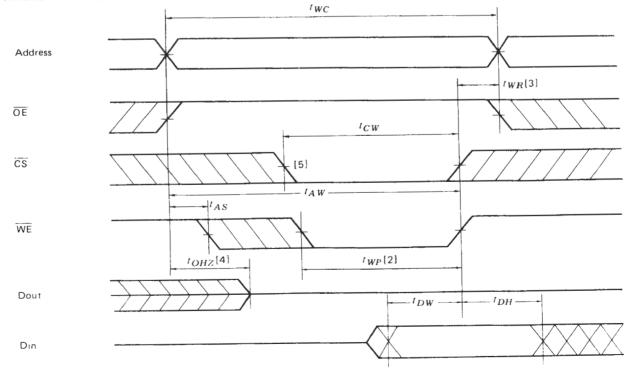


- NOTES: 1. WE is High for Read Cycle.
 2. Device is continuously selected, CS = V_{IL}
 3. Address Valid prior to or coincident with CS transition Low.
 - 4. When CS is Low, the address input must not be in the high impedance state.

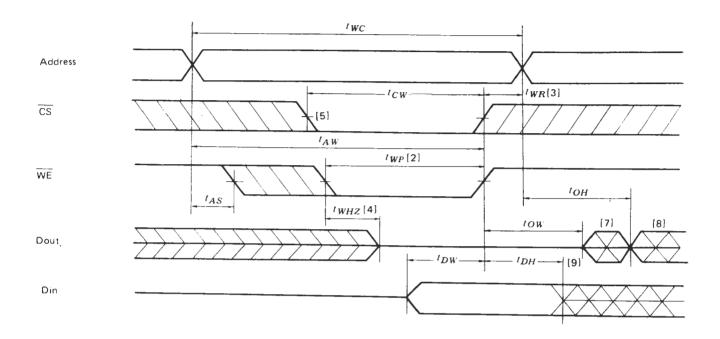
• WRITE CYCLE

	Symbol	НМ6	116P-2	HM6116P-3		HM6116P-4		
Parameter		Min	Max	Min	Max	Min	Max	Unit
Write Cycle Time	. Iwc	120	_	150	_	200		ns
Chip Selection to End of Write	tcs	70		90		120		ns
Address Valid to End of Write	<i>t</i> ,410°	105		120		140	_	ns
Address Set Up Time	tas	20	!	20		20	_	ns
Write Pulse Width	I u·p	70	-	90		120		ns
Write Recovery Time	1 WR	5		10	_	10	_	ns
Output Disable to Output in High Z	toHZ	0	40	0	50	0	60	ns
Write to Output in High Z	I WHZ	0	50	0	60	0	60	ns
Data to Write Time Overlap	t_{DW}	35		40	-	60		ns
Data Hold from Write Time	I DH	5	_	10	. —	10	_	ns
Output Active from End of Write	tow	5	_	10		10	-	ns

■ TIMING WAVEFORM OF WRITE CYCLE NO. 11



■ TIMING WAVEFORM OF WRITE CYCLE NO. 21,6



NOTES: 1. WE must be high during all address transitions.

- 2. A write occurs during the overlap (twp) of a low CS and a low WE.
- 3. twn is measured from the earlier of CS or WE going high to the end of write cycle.
- 4. During this period, I/O pins are in the output state so that the input signals of opposite phase to the outputs must not be applied.
- 5. If the CS low transition occurs simultaneously with the WE low transitions or after the WE transition, output remain in a high impedance state.
- 6. OE is continuously low. (OE = V_{IL})
- 7. Dout is the same phase of write data of this write cycle.
- 8. Dout is the read data of next address.
- 9. If CS is low during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.

m.T. Wingfit

MPM SET-UP (48K BANKED, 16K TOP COMMON)

· 48K BANKED SLAVE MEMORY, Top 16K MEMORY COMMON.

SET UP THE MB64 PER 2.9.5 EXCEPT FOR THE FOLLOWING:

a) Do NOT REMOVE ANY RAM CHIPS.

B) DO NOT JUMPER E30 to E31.

C) SET TOP 8K FOR RAM.

ESC to E51

E53 to E57

E59 to E57

B59 to E60

B59 to E60

B59 to E60

B31 to U37 PIN 1 (741532)

E30 to U37 PIN 3

U31 PIN 20 to U37 PIN 2

(FROM BANK)

FLIP-FLOP)

U37

E31>

E30

(A14 ADDRESS)

(U31-20)